

# SILICON TRANSISTOR 2SC2351

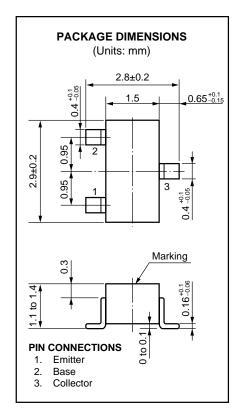
# HIGH FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR MINI MOLD

#### **FEATURES**

NF 1.5 dB TYP. @ f = 1.0 GHz
 MAG 14 dB TYP. @ f = 1.0 GHz

### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Collector to Base Voltage	Vсво	25	V
Collector to Emitter Voltage	VCEO	12	V
Emitter to Base Voltage	Vево	3.0	V
Collector Current	Ic	70	mΑ
Total Power Dissipation	Рт	250	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>sta</sub>	-65 to +150	°C



## ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
CHARACTERISTIC	STIVIBUL	IVIIIN.	ITP.	WAA.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			0.1	μΑ	Vcb = 15 V, IE = 0
Emitter Cutoff Current	ІЕВО			0.1	μΑ	V <sub>EB</sub> = 2.0 V, I <sub>C</sub> = 0
DC Current Gain	hfe	40		200		Vce = 10 V, Ic = 20 mA
Gain Bandwidth Product	f⊤		4.5		GHz	Vce = 10 V, Ic = 20 mA
Output Capacitance	Cob		0.75	1.0	pF	Vcb = 10 V, IE = 0, f = 1.0 MHz
Insertion Power Gain	S <sub>21</sub> e  <sup>2</sup>	9	11		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.5	3.0	dB	Vce = 10 V, Ic = 5 mA, f = 1.0 GHz
Maximum Available Gain	MAG		14		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz

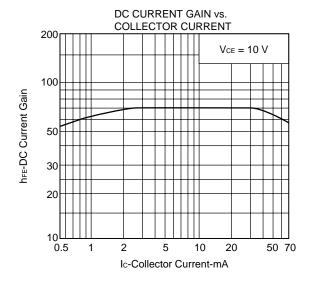
#### **hfe Classification**

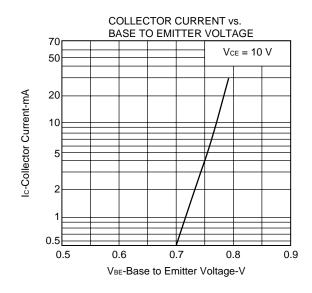
0.000000				
Class	E/P *	F/Q *		
Marking	R2	R3		
hfe	40 to 120	100 to 200		

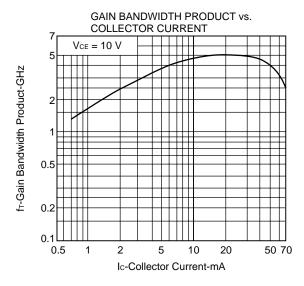
<sup>\*</sup> Old Specification / New Specification

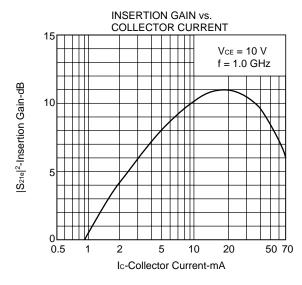


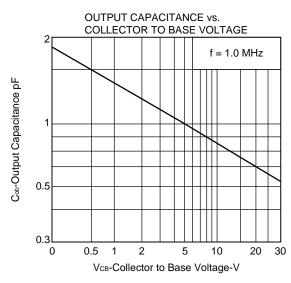
### TYPICAL CHARACTERISTICS (TA = 25 °C)

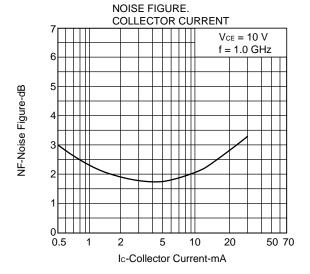


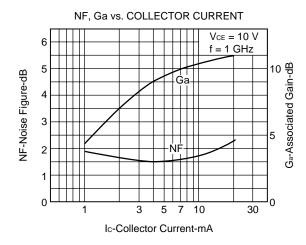












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- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.

M4 96.5